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April 1<sup>st</sup>, 2010 Renesas Electronics Corporation

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# RENESAS

# MOS FIELD EFFECT TRANSISTOR $\mu \, PA679TB$

## N/P-CHANNEL MOS FIELD EFFECT TRANSISTOR FOR SWITCHING

#### DESCRIPTION

The  $\mu$  PA679TB is a switching device, which can be driven directly by a 2.5 V power source.

The  $\mu$  PA679TB features a low on-state resistance and excellent switching characteristics, and is suitable for applications such as power switch of portable machine and so on.

#### **FEATURES**

- 2.5 V drive available
- Low on-state resistance
- P-ch R<sub>DS(on)1</sub> = 1.45 Ω MAX. (V<sub>GS</sub> = -4.5 V, I<sub>D</sub> = -0.20 A) R<sub>DS(on)3</sub> = 2.98 Ω MAX. (V<sub>GS</sub> = -2.5 V, I<sub>D</sub> = -0.15 A)
- Two MOS FET circuits in same size package as SC-70

#### **ORDERING INFORMATION**

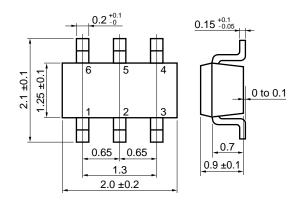
PART NUMBER	PACKAGE		
$\mu$ PA679TB	SC-88 (SSP)		

#### Marking: YA

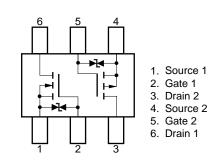
#### ABSOLUTE MAXIMUM RATINGS (TA = 25°C)

Drain to Source Voltage (VGs = 0 V)	VDSS	20 /20	V
Gate to Source Voltage (VDS = 0 V)	Vgss	±12 / ∓12	V
Drain Current (DC)	ID(DC)	±0.35 / ∓0.25	Α
Drain Current (pulse) Note1	D(pulse)	±1.40 / ∓1.00	А
Total Power Dissipation (2 units) Note2	Р⊤	0.2	W
Channel Temperature	Tch	150	°C
Storage Temperature	Tstg	–55 to +150	°C

#### PACKAGE DRAWING (Unit: mm)



#### **PIN CONNECTION (Top View)**



**Notes 1.** PW  $\leq$  10  $\mu$ s, Duty Cycle  $\leq$  1%

- 2. Mounted on FR-4 board of 2500 mm<sup>2</sup> x 1.1 mm
- **Remark** The diode connected between the gate and source of the transistor serves as a protector against ESD. When this device actually used, an additional protection circuit is externally required if a voltage exceeding the rated voltage may be applied to this device.
- Caution This product is electrostatic-sensitive device due to low ESD capability and shoud be handled with caution for electrostatic discharge.  $V_{ESD} = \pm 100 \text{ V TYP.}$  (C = 200 pF, R = 0  $\Omega$ , Single pulse)

 $VESD = \pm 100 V TTP. (C = 200 pr, R = 0.22, Single pulse)$ 

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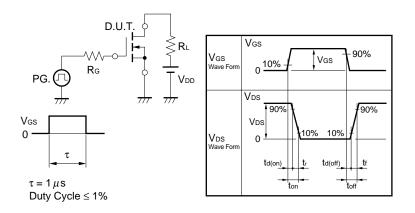
#### **ELECTRICAL CHARACTERISTICS**

### (1) N-ch PART (T<sub>A</sub> = 25°C)

CHARACTERISTICS	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Zero Gate Voltage Drain Current	loss	V <sub>DS</sub> = 20.0 V, V <sub>GS</sub> = 0 V			1.0	μA
Gate Leakage Current	lgss	V <sub>GS</sub> = ±12.0 V, V <sub>DS</sub> = 0 V			±10	μA
Gate Cut-off Voltage Note	V <sub>GS(off)</sub>	V <sub>DS</sub> = 10.0 V, I <sub>D</sub> = 1.0 mA	0.50	1.00	1.50	V
Forward Transfer Admittance Note	y <sub>fs</sub>	V <sub>DS</sub> = 10.0 V, I <sub>D</sub> = 0.30 A	0.25	0.75		S
Drain to Source On-state Resistance Note	RDS(on)1	V <sub>GS</sub> = 4.5 V, I <sub>D</sub> = 0.30 A		0.38	0.57	Ω
	RDS(on)2	V <sub>GS</sub> = 4.0 V, I <sub>D</sub> = 0.30 A		0.41	0.60	Ω
	RDS(on)3	V <sub>GS</sub> = 2.5 V, I <sub>D</sub> = 0.15 A		0.60	0.88	Ω
Input Capacitance	Ciss	V <sub>DS</sub> = 10.0 V		28		pF
Output Capacitance	Coss	V <sub>GS</sub> = 0 V		11		pF
Reverse Transfer Capacitance	Crss	f = 1.0 MHz		7		pF
Turn-on Delay Time	td(on)	V <sub>DD</sub> = 10.0 V, I <sub>D</sub> = 0.30 A		20		ns
Rise Time	tr	V <sub>GS</sub> = 4.0 V		51		ns
Turn-off Delay Time	td(off)	R <sub>G</sub> = 10 Ω		94		ns
Fall Time	tr			87		ns
Body Diode Forward Voltage	VF(S-D)	I⊧ = 0.35 A, V₀s = 0 V		0.84		V

**Note** Pulsed: PW  $\leq$  350  $\mu$ s, Duty cycle  $\leq$  2%

#### TEST CIRCUIT SWITCHING TIME

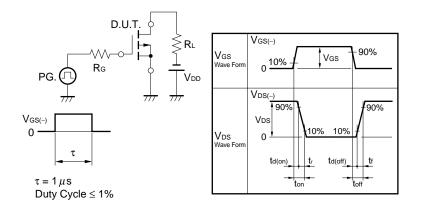


#### (2) P-ch PART (T<sub>A</sub> = 25°C)

CHARACTERISTICS	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Zero Gate Voltage Drain Current	IDSS	V <sub>DS</sub> = -20.0 V, V <sub>GS</sub> = 0 V			-1.0	μA
Gate Leakage Current	lgss	V <sub>GS</sub> = ∓12.0 V, V <sub>DS</sub> = 0 V			<b>∓10</b>	μA
Gate Cut-off Voltage Note	V <sub>GS(off)</sub>	V <sub>DS</sub> = -10.0 V, I <sub>D</sub> = -1.0 mA	-0.80	-1.30	-1.80	V
Forward Transfer Admittance Note	y <sub>fs</sub>	V <sub>DS</sub> = -10.0 V, I <sub>D</sub> = -0.20 A	0.2	0.6		S
Drain to Source On-state Resistance Note	RDS(on)1	V <sub>GS</sub> = -4.5 V, I <sub>D</sub> = -0.20 A		1.17	1.45	Ω
	RDS(on)2	V <sub>GS</sub> = -4.0 V, I <sub>D</sub> = -0.20 A		1.25	1.55	Ω
	RDS(on)3	V <sub>GS</sub> = -2.5 V, I <sub>D</sub> = -0.15 A		2.25	2.98	Ω
Input Capacitance	Ciss	V <sub>DS</sub> = -10.0 V		29		pF
Output Capacitance	Coss	V <sub>GS</sub> = 0 V		15		pF
Reverse Transfer Capacitance	Crss	f = 1.0 MHz		3		pF
Turn-on Delay Time	td(on)	V <sub>DD</sub> = -10.0 V, I <sub>D</sub> = -0.20 A		23		ns
Rise Time	tr	V <sub>GS</sub> = -4.0 V		39		ns
Turn-off Delay Time	td(off)	R <sub>G</sub> = 10 Ω		50		ns
Fall Time	tr			33		ns
Body Diode Forward Voltage	VF(S-D)	IF = 0.25 A, VGS = 0 V		0.88		V

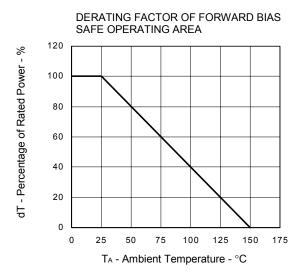
**Note** Pulsed: PW  $\leq$  350  $\mu$ s, Duty cycle  $\leq$  2%

#### TEST CIRCUIT SWITCHING TIME

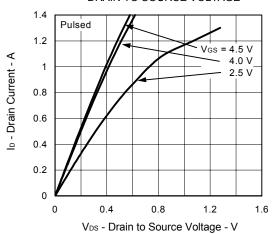


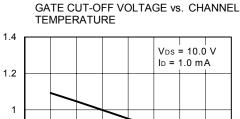
#### **TYPICAL CHARACTERISTICS**

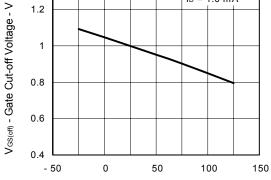
#### (1) N-ch PART ( $T_A = 25^{\circ}C$ )



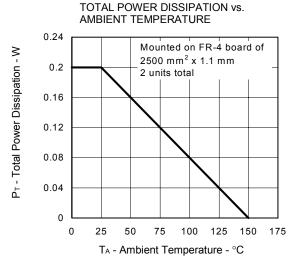




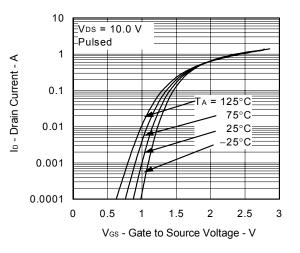




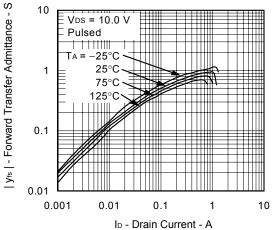
T<sub>ch</sub> - Channel Temperature - °C



FORWARD TRANSFER CHARACTERISTICS



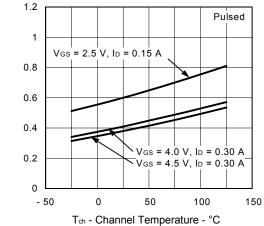
FORWARD TRANSFER ADMITTANCE vs. DRAIN CURRENT





 $R_{DS(m)}$  - Drain to Source On-state Resistance -  $\Omega$ 

DRAIN TO SOURCE ON-STATE RESISTANCE vs. CHANNEL TEMPERATURE



DRAIN TO SOURCE ON-STATE RESISTANCE vs.

Vgs = 4.5 V

Pulsed

1

DRAIN CURRENT

TA = 125°C

75°C

25°C

-25°C

0.1

1.2

1

0.8

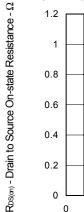
0.6

0.4

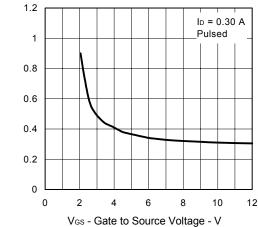
0.2

0

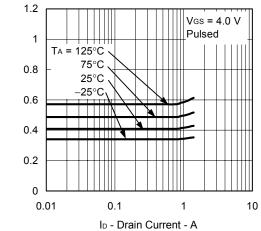
0.01

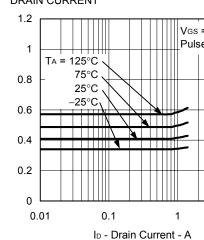


DRAIN TO SOURCE ON-STATE RESISTANCE vs. GATE TO SOURCE VOLTAGE



DRAIN TO SOURCE ON-STATE RESISTANCE vs. DRAIN CURRENT





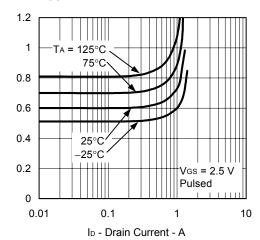
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 $R_{DS(cn)}$  - Drain to Source On-state Resistance -  $\Omega$ 

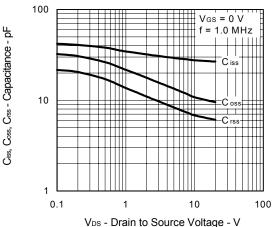
DRAIN TO SOURCE ON-STATE RESISTANCE vs. DRAIN CURRENT

ID - Drain Current - A

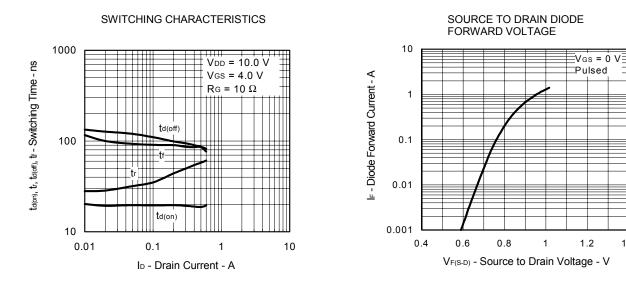
 $\mathsf{R}_{\mathsf{DS}(m)}$  - Drain to Source On-state Resistance -  $\Omega$ 



CAPACITANCE vs. DRAIN TO SOURCE VOLTAGE

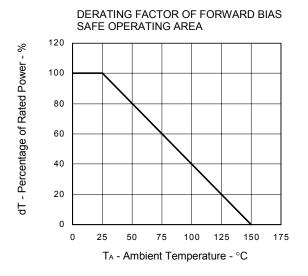


1.4



#### Data Sheet G16615EJ1V0DS

#### (2) P-ch PART (T<sub>A</sub> = 25°C)



DRAIN CURRENT vs.

- 1

- 0.8

- 0.6

- 0.4

- 0.2

0

0

Ip - Drain Current - A

Pulsed

Vgs = -4.5 V

- 0.4

- 0.8

DRAIN TO SOURCE VOLTAGE

-4.0 V

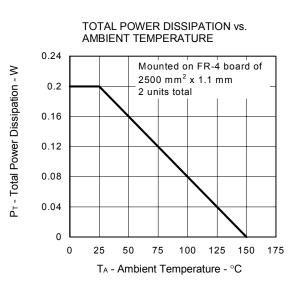
–2.5 V

- 1.6

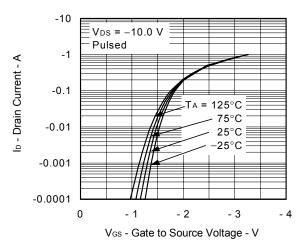
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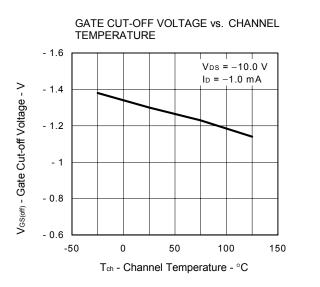
- 1.2

VDS - Drain to Source Voltage - V

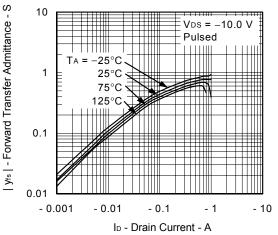


FORWARD TRANSFER CHARACTERISTICS





FORWARD TRANSFER ADMITTANCE vs. DRAIN CURRENT

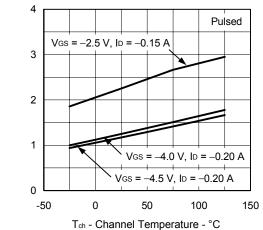




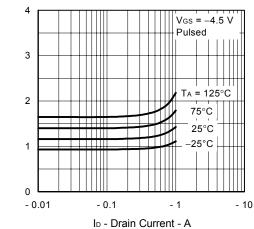


 $\mathsf{R}^{\mathsf{DS}(m)}$  - Drain to Source On-state Resistance -  $\Omega$ 

DRAIN TO SOURCE ON-STATE RESISTANCE vs. CHANNEL TEMPERATURE

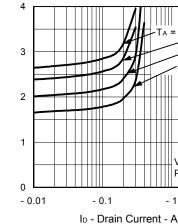


DRAIN TO SOURCE ON-STATE RESISTANCE vs. DRAIN CURRENT



DRAIN TO SOURCE ON-STATE RESISTANCE vs. DRAIN CURRENT

- 1



Ciss, Coss, Crss - Capacitance - pF 125°C = 75°C 25°C 25°C Vgs = -2.5 V Pulsed

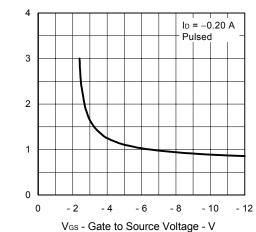
- 10

4 3 2 1 0 0 - 2 - 4

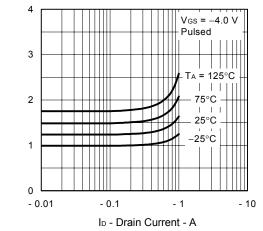
 $R_{DS(cn)}$  - Drain to Source On-state Resistance -  $\Omega$ 

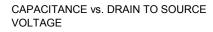
 $R_{DS(m)}$  - Drain to Source On-state Resistance -  $\Omega$ 

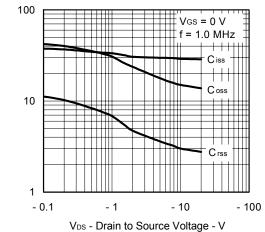
#### DRAIN TO SOURCE ON-STATE RESISTANCE vs. GATE TO SOURCE VOLTAGE



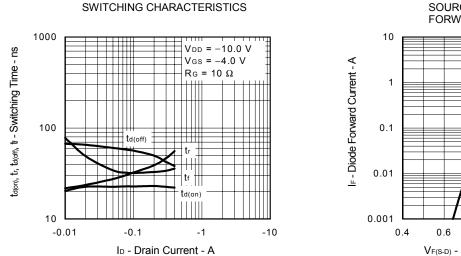
DRAIN TO SOURCE ON-STATE RESISTANCE vs. DRAIN CURRENT



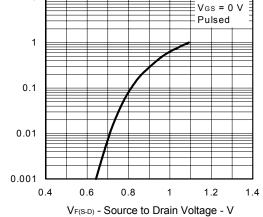




 $R_{DS(cn)}$  - Drain to Source On-state Resistance -  $\Omega$ 



#### SOURCE TO DRAIN DIODE FORWARD VOLTAGE



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